Amendments to the Claims:

This listing of claims will replace all prior versions, and listing, of claims in the application:

Listing of Claims:

1-64. Cancelled.

65. (new) A device comprising a nanowire, an electrical contact, and an ohmic contact electrically coupling the nanowire and the electrical contact, wherein the ohmic contact comprises at least one metal silicide.

66. (new) The device of claim 65, wherein the at least one metal silicide comprises titanium silicide.

67. (new) The device of claim 65, wherein the at least one metal silicide comprises nickel silicide.

68. (new) The device of claim 65, wherein the ohmic contact comprises a sacrificial layer between the nanowire and the electrical contact.

69. (new) The device of claim 68, wherein the sacrificial layer comprises poly or amorphous doped silicon.

70. (new) The device of claim 65, wherein the ohmic contact comprises at least a portion of the nanowire.

71. (new) The device of claim 70, wherein the nanowire has at least one dimension less than or equal to 500 nm.

72. (new) The device of claim 70, wherein the nanowire has at least one dimension less than or equal to 200 nm.

73. (new) The device of claim 70, wherein the nanowire comprises silicon.

74. (new) The device of claim 65, wherein the ohmic contact comprises a metal selected from the group comprising titanium, platinum, chromium, nickel, aluminum, copper and gold.

75. (new) A device comprising one or more nanowire which is electrically coupled to an electrode contact at a metal silicide junction.

76. (new) The device of claim 75, wherein the metal is selected from the group comprising titanium, platinum, nickel, chromium, aluminum, copper and gold.

77. (new) The device of claim 75, wherein the metal silicide junction comprises a sacrificial layer between the nanowire and the electrical contact.

78. (new) The device of claim 75, wherein the nanowire is in direct contact to the electrode contact at the junction.

79. (new) The device of claims 75, wherein the device comprises a nanosensor.

80. (new) The device of claim 79, wherein the nanosensor comprises a glucose nanoosensor comprising the one or more nanowires and glucose oxidase, wherein the glucose oxidase is proximal to the one or more nanowires or immobilized on the one or more nanowires.

81. (new) The device of claim 79, wherein the nanosensor comprises an array for detection of a change in charge, the array comprising a plurality of nanowires, which nanowires each comprise one or more functional group, which functional group undergoes a change in charge when exposed to a component of interest.

82. (new) A method of reducing an ohmic contact resistance at a junction between a nanowire and an electrical contact comprising forming said junction from at least one metal silicide.

83. (new) The method of claim 82, wherein the at least one metal silicide comprises titanium silicide.

84. (new) The method of claim 82, wherein the at least one metal silicide comprises nickel silicide.

85. (new) The method of claim 82, wherein the at least one metal silicide comprises platinum silicide.

86. (new) The method of claim 82, wherein the at least one metal silicide comprises tantalum silicide.

87. (new) The method of claim 82, wherein forming said junction comprises forming a sacrificial layer between the nanowire and the electrical contact, wherein the sacrificial layer comprises the at least one metal silicide.

88. (new) The method of claim 87, wherein the nanowire is electrically coupled to the electrode contact via said sacrificial layer.

89. (new) The method of claim 82, wherein the junction comprises a metal selected from the group comprising titanium, platinum, chromium, nickel, aluminum, copper and gold.

90. (new) The method of claim 82, wherein the junction further comprises one or more dopant materials.

91. (new) The method of claim 82, wherein the nanowire makes direct contact to the electrical contact at said junction.